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Hong et al.

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(54) **FLATTENING METHOD OF A SUBSTRATE**

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(52) **U.S. Cl.**
USPC **438/160**; 257/E21.561; 438/30

(58) **Field of Classification Search**
USPC 438/151-166, 30; 257/E21.561
See application file for complete search history.

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(57) **ABSTRACT**

A method of flattening a substrate includes forming a metal layer on an upper surface of a substrate, forming a photoresist layer covering the substrate and the metal layer, radiating light to the photoresist layer, through a lower surface of the substrate opposite to the upper surface, exposing the metal layer by developing the photoresist layer, exposing the upper surface of the substrate by etching the metal layer, etching the exposed upper surface of the substrate, and removing the photoresist layer.

18 Claims, 7 Drawing Sheets

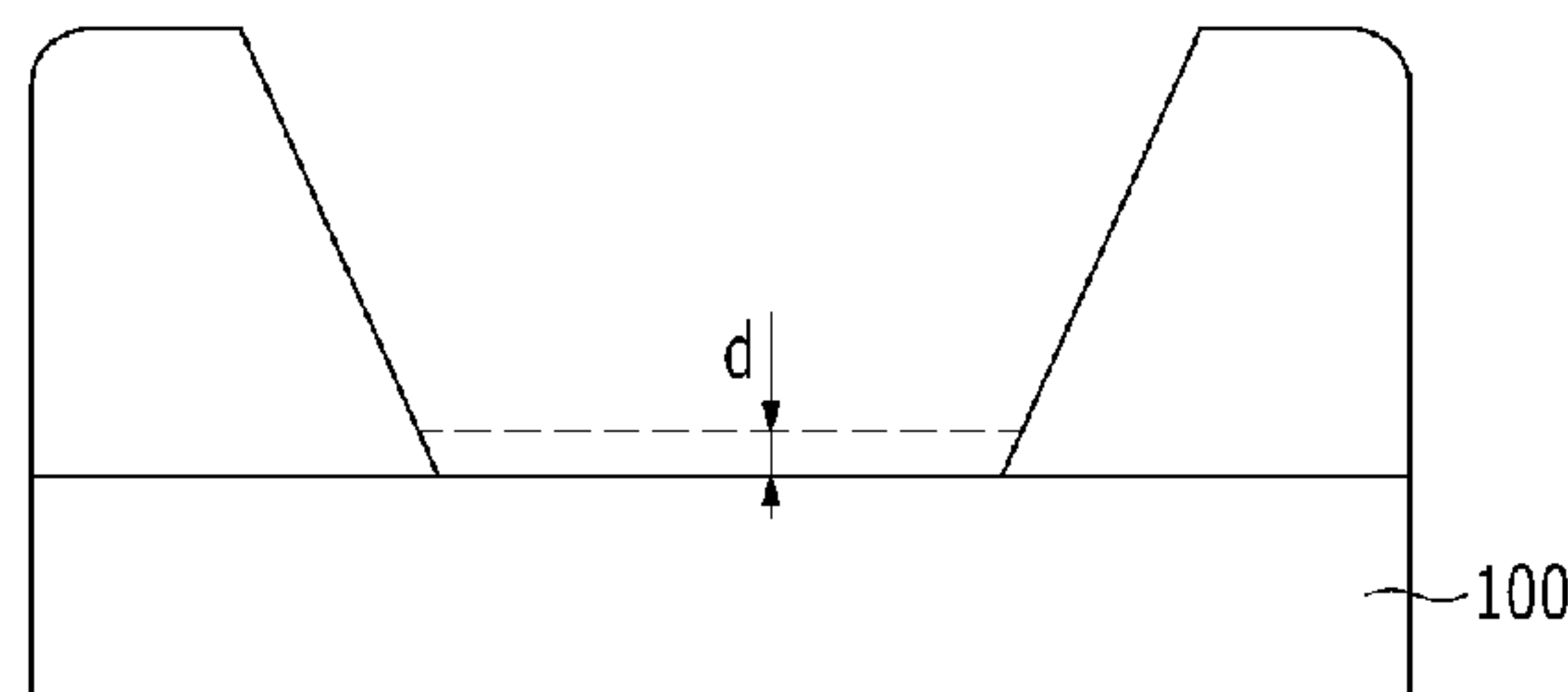
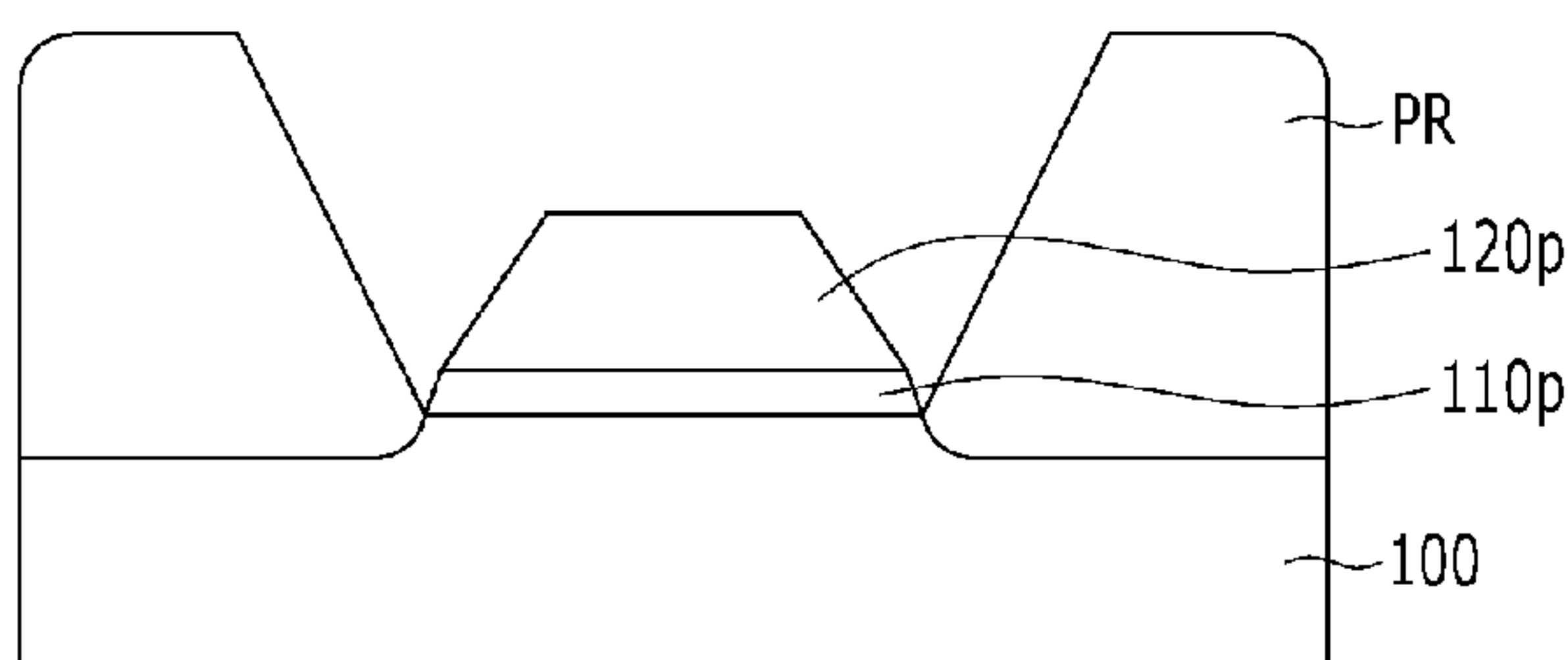


FIG. 1

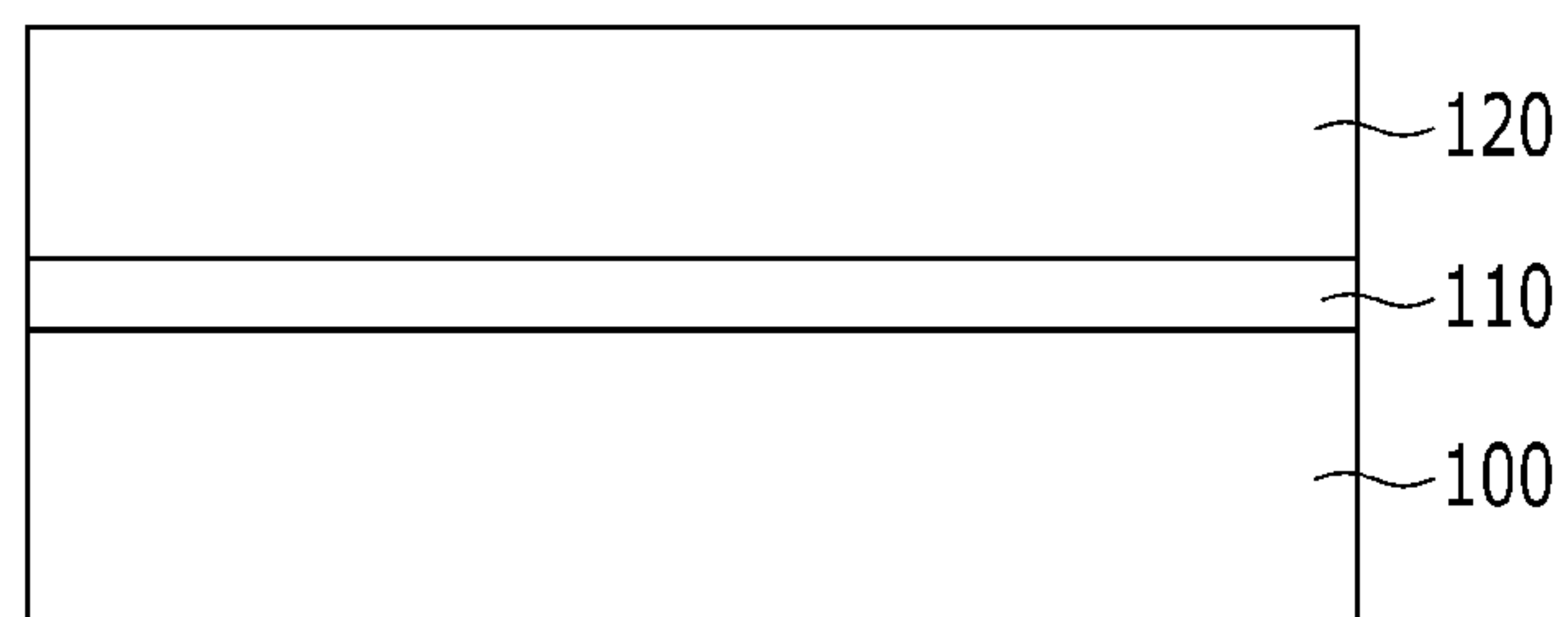


FIG. 2

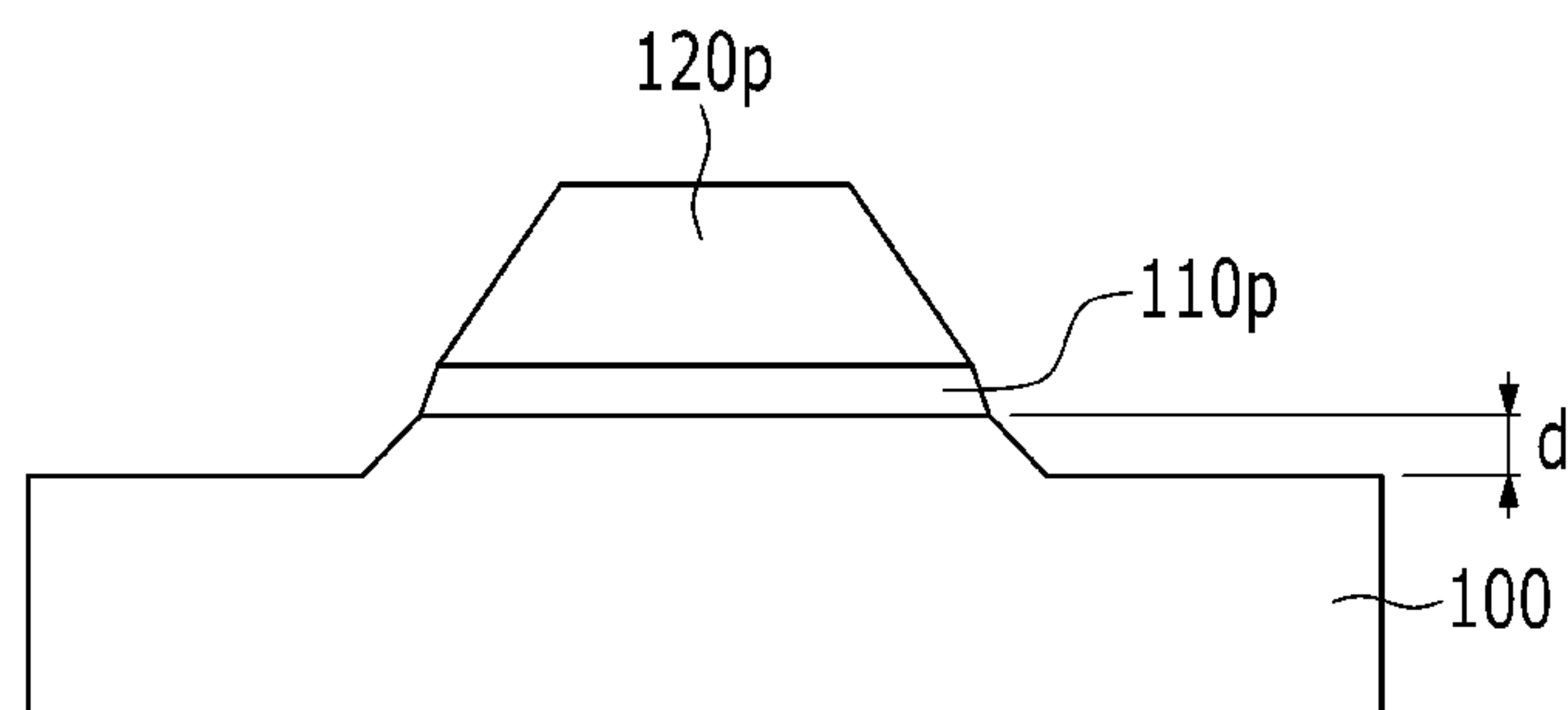


FIG. 3

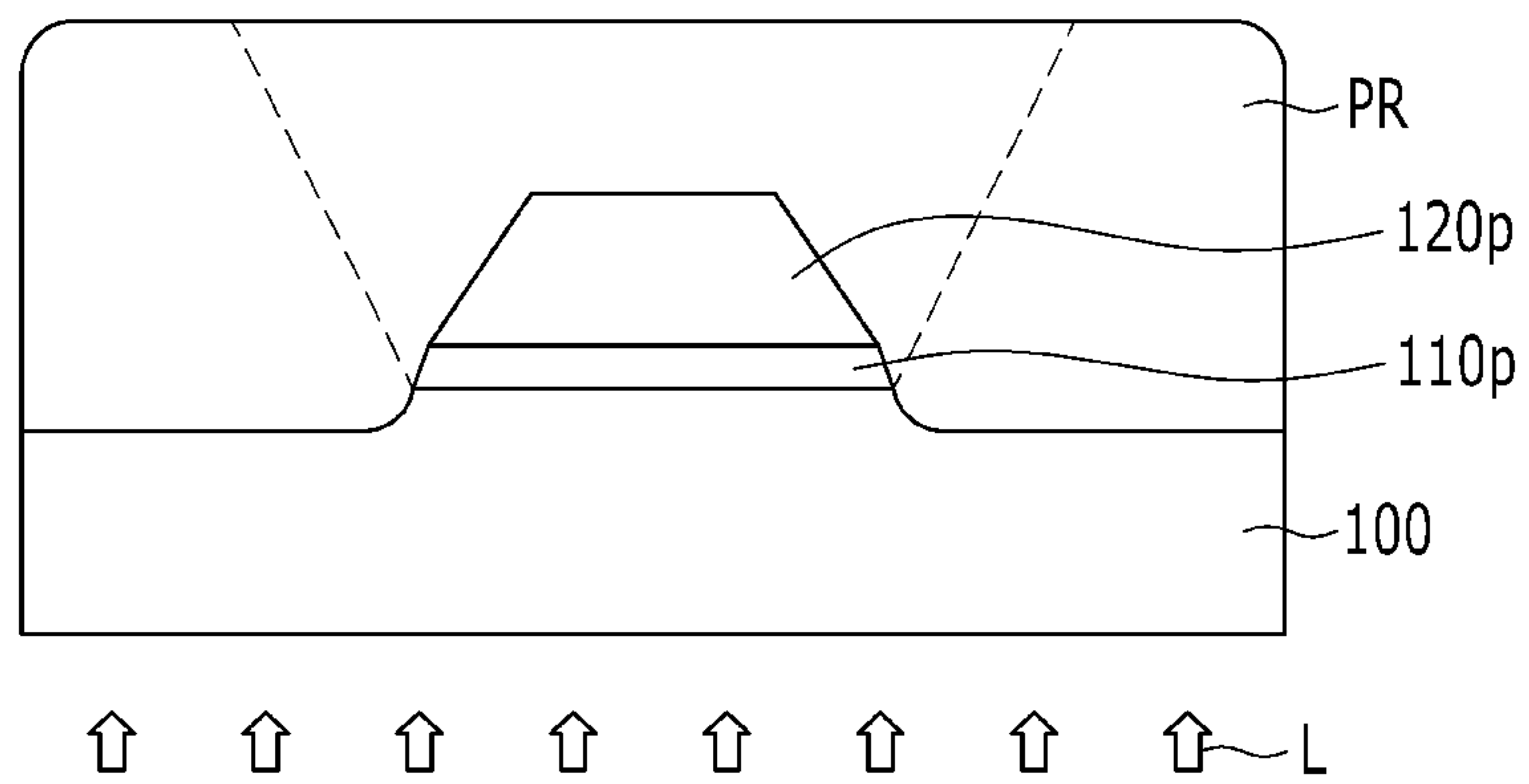


FIG. 4

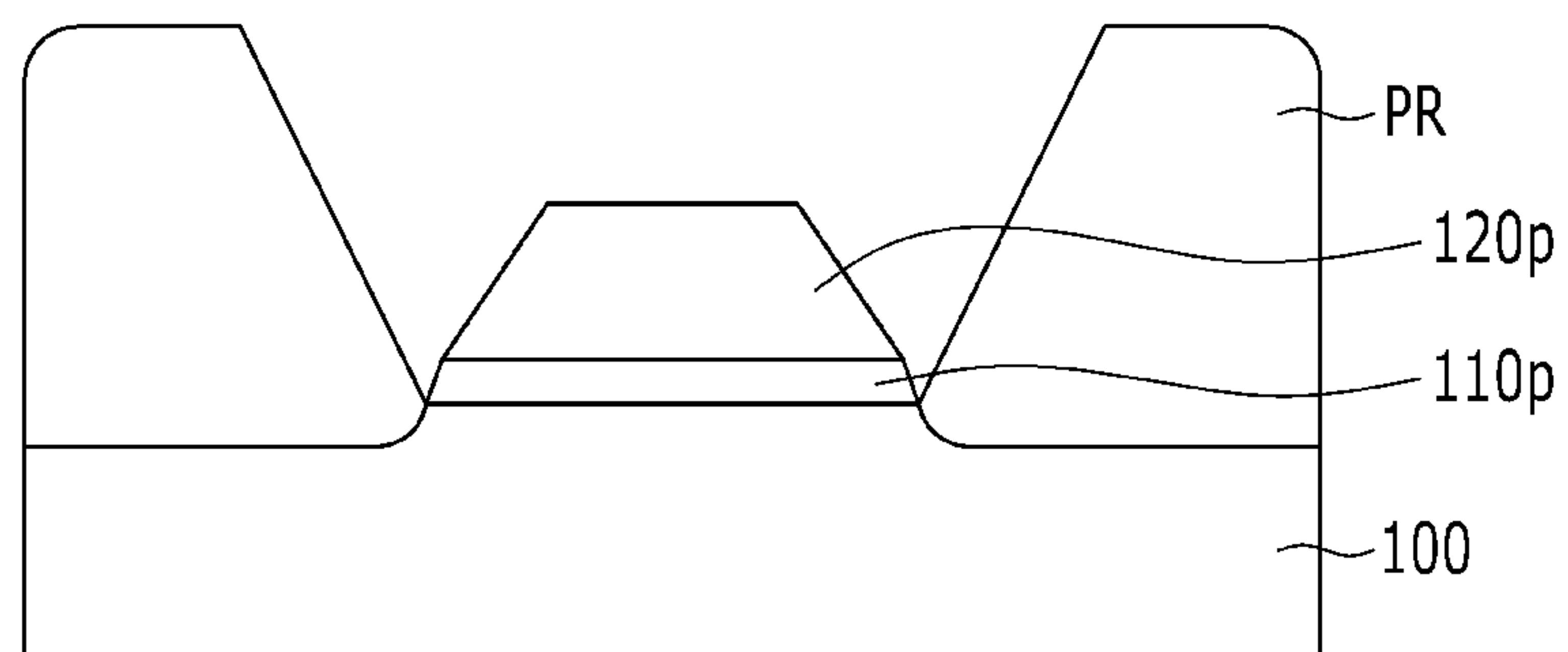


FIG. 5

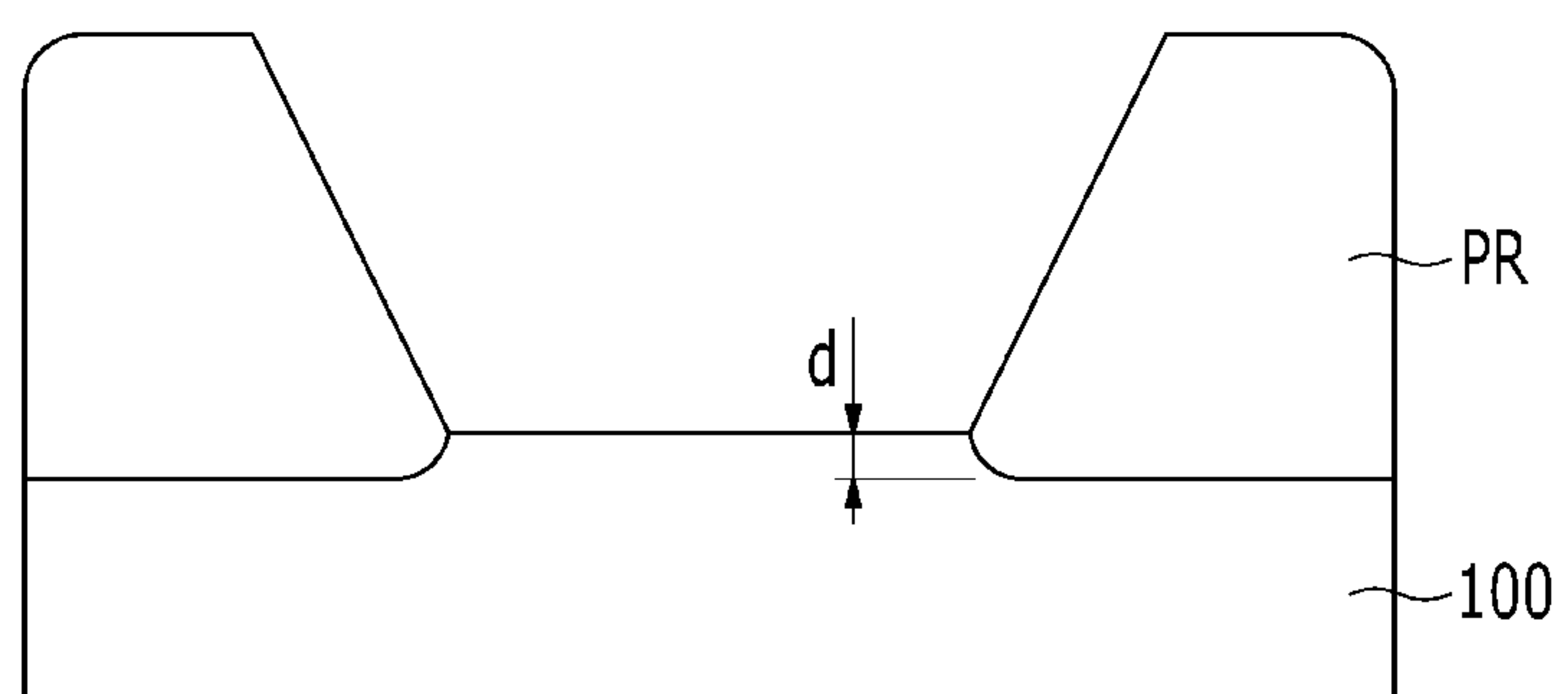


FIG. 6

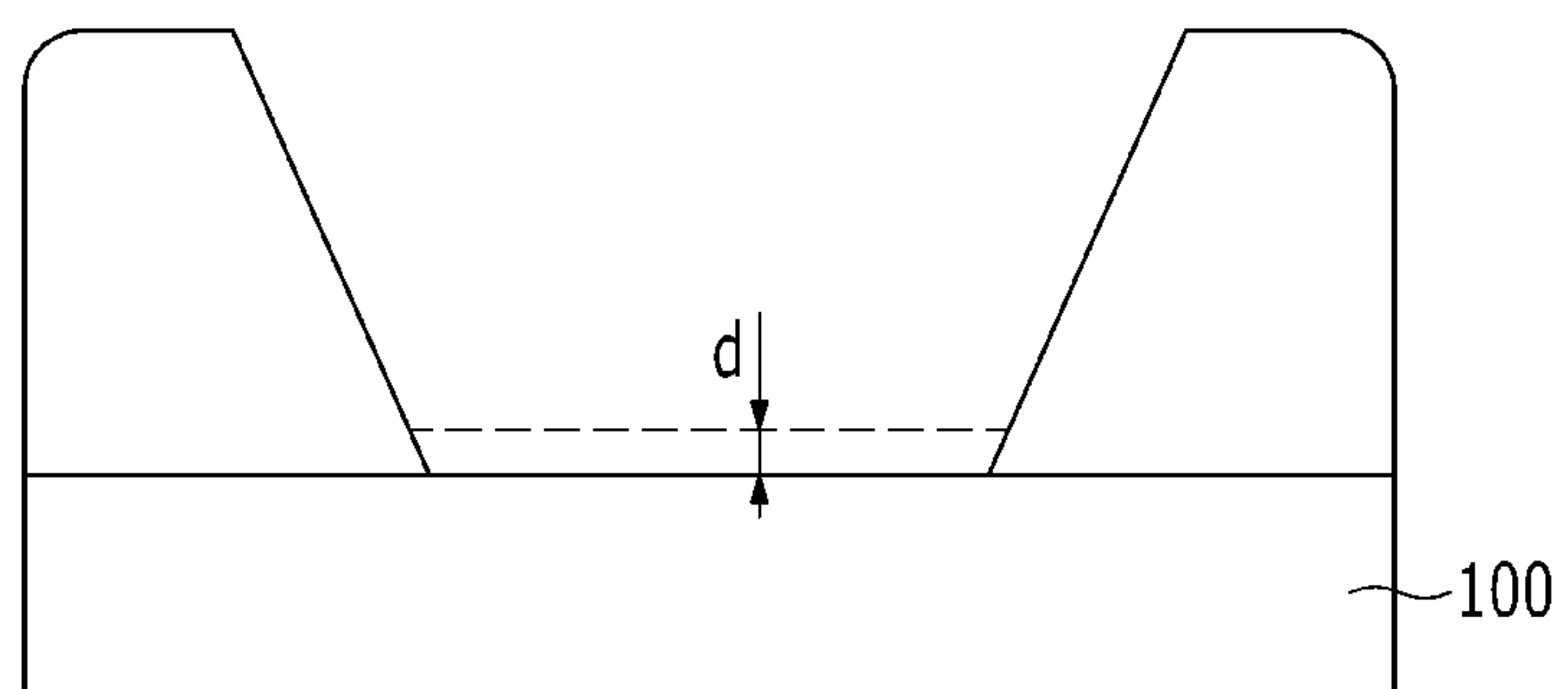


FIG. 7

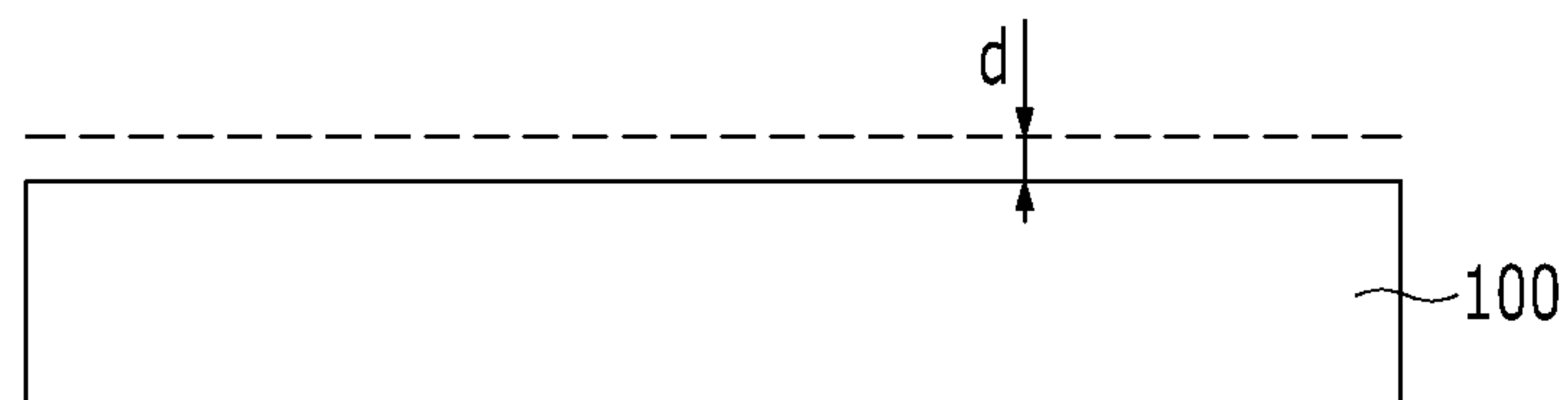


FIG. 8

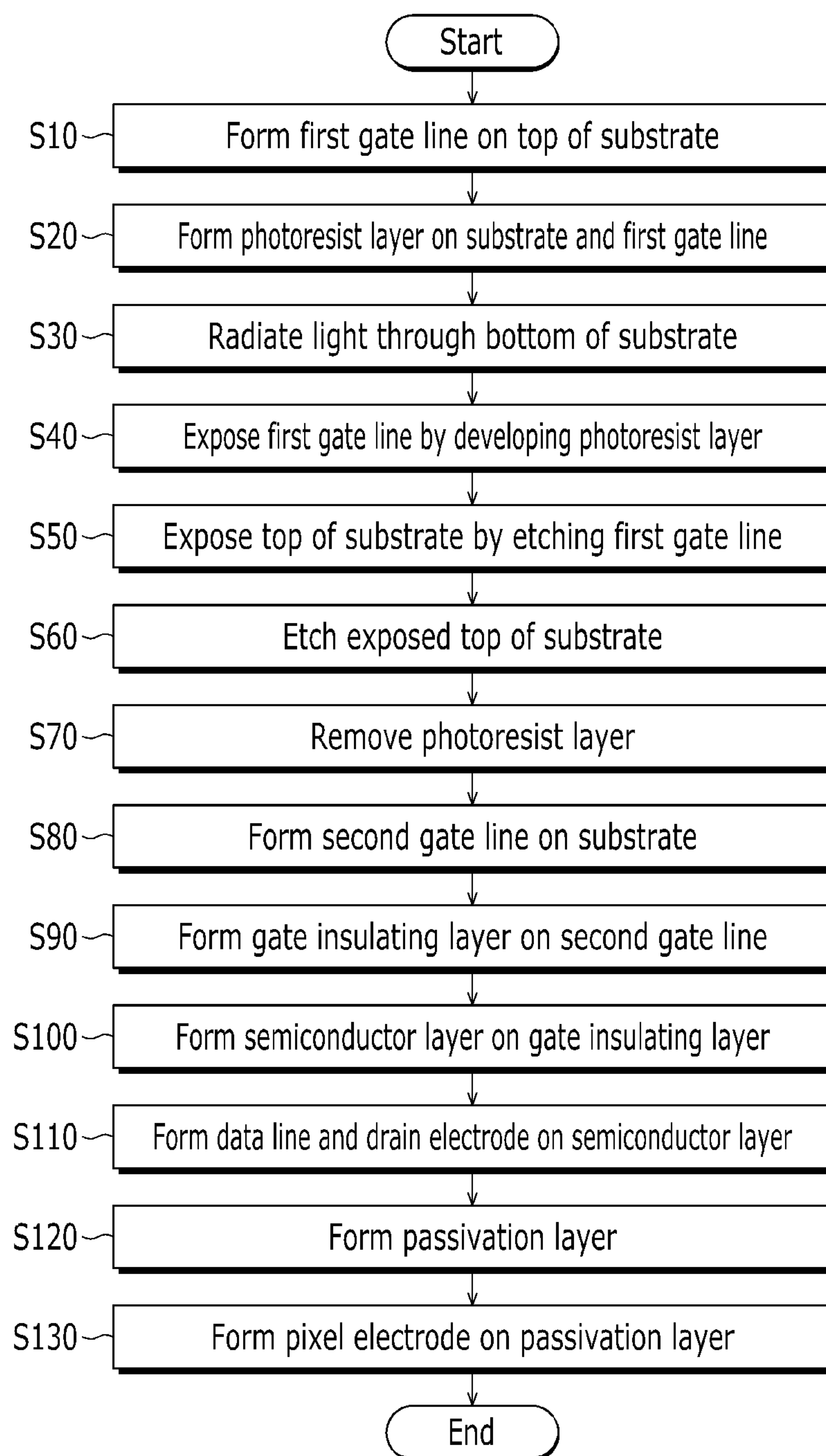


FIG. 9

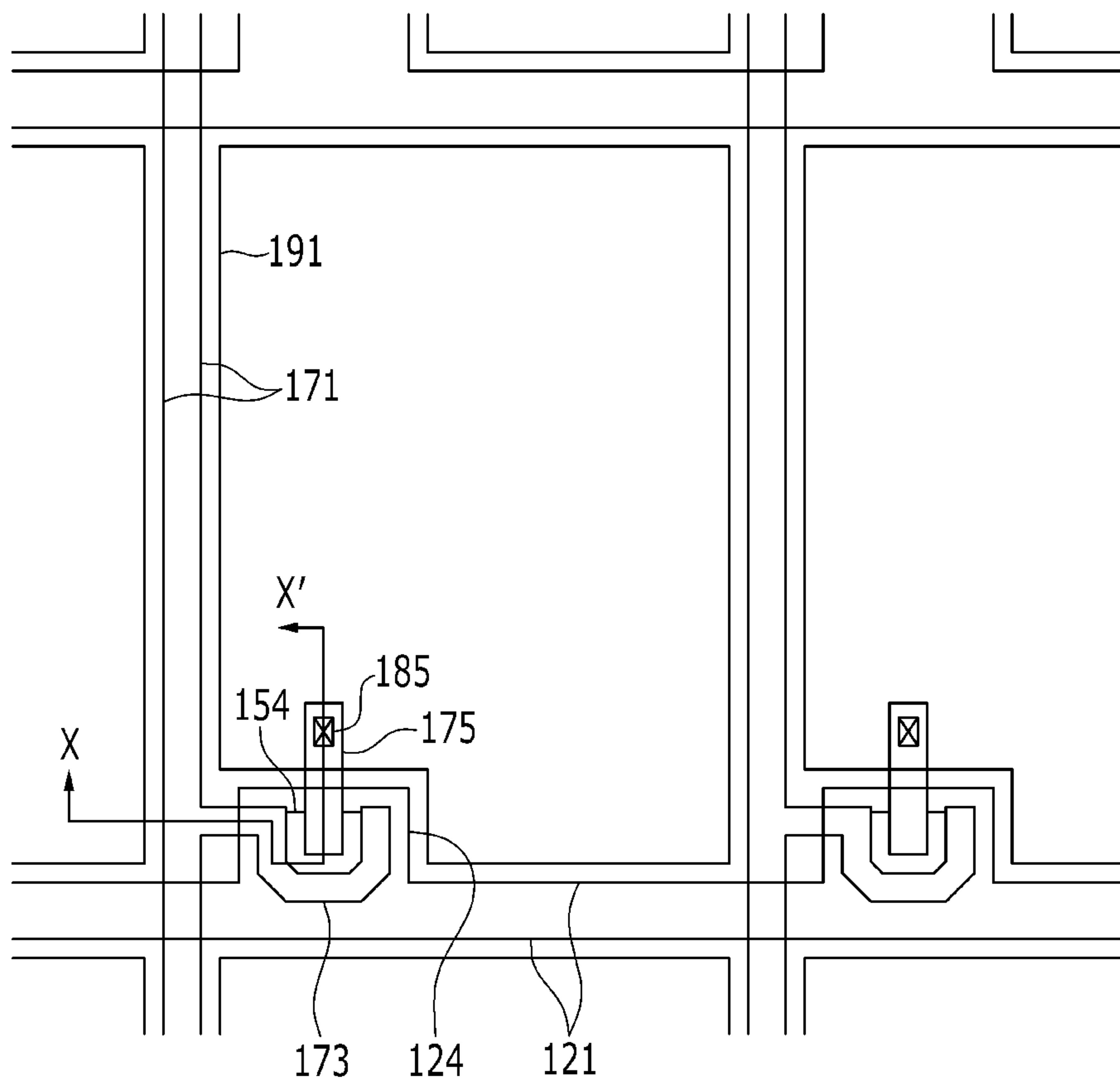
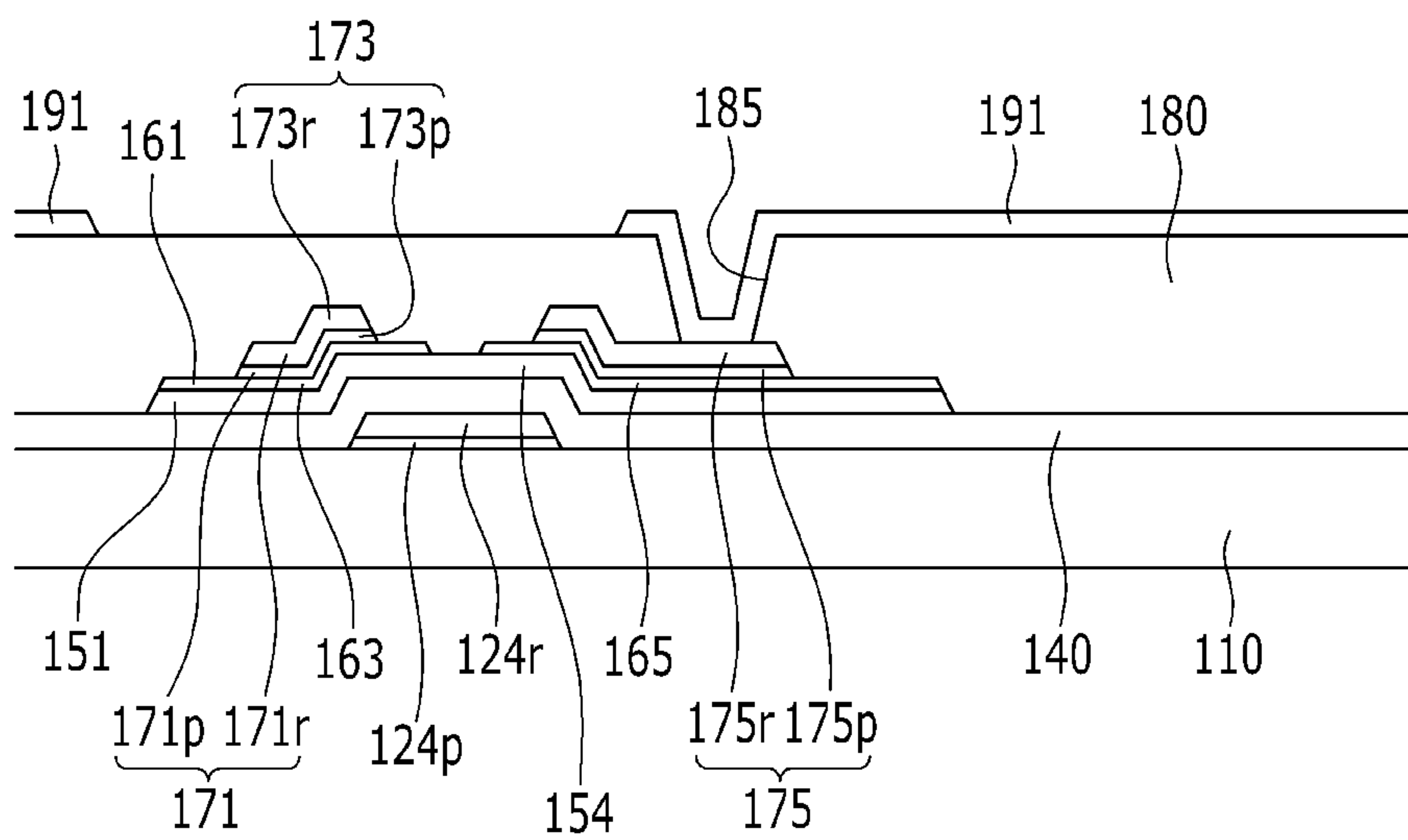


FIG. 10



FLATTENING METHOD OF A SUBSTRATE

This application claims priority to Korean Patent Application No. 10-2010-0126287 filed on Dec. 10, 2010, and all the benefits accruing therefrom under 35 U.S.C. §119, the entire contents of which are incorporated herein by reference.

BACKGROUND OF THE INVENTION**(1) Field of the Invention**

The present invention relates to a flattening method of a substrate, and a method of manufacturing a thin film transistor array panel using the same.

(2) Description of the Related Art

In general, thin film transistor array panels are used as circuit boards for independently driving pixels in liquid crystal displays or organic electro luminescence (“EL”) display devices. The thin film transistor array panels include a gate wire transmitting scan signals, a data wire transmitting image signals, a thin film transistor connected with the gate wire and the data wire, and a pixel electrode connected with the thin film transistor.

The thin film transistor is composed of a semiconductor layer forming a channel, a gate electrode of the gate wire, and a source electrode and a drain electrode of the data wire. The thin film transistor is a switching element that transmits or blocks data voltage transmitted through the data wire to the pixels, in response to a gate signal transmitted through the gate wire.

In manufacturing the thin film transistor, a metal layer is stacked first on a substrate as a wiring material for a gate or a source/drain electrode, and the metal layer is etched for implementing desired lines of an electric circuit. In the manufacturing process, portions of the metal layer are removed by using a gas or solution having corrosiveness.

The wires become narrow with the reduction in size and integration of the circuit, such that electrical resistance is relatively increased. Accordingly, copper has been under the spotlight as a row-resistant wiring material, instead of chromium, molybdenum, aluminum and alloys of them, which have been generally used as wiring materials in the related art.

However, copper does not bond well with a glass substrate or a silicon insulating layer, and is difficult to use in a single layer structure. A multilayer structure including the copper has been proposed. The multilayer structure uses a metal layer that bonds well with a glass substrate or a silicon insulating layer, for example a titanium layer, as a lower layer between the copper and the respective glass substrate or silicon insulating layer.

Etching solution containing fluoric acid is used to etch the entire multilayer. However, the etching solution containing fluoric acid etches not only the wires, but the substrate thereunder and leaves stains in subsequent manufacturing processes.

The above information disclosed in this Background section is only for enhancement of understanding of the background of the invention and therefore it may contain information that does not form the prior art that is already known in this country to a person of ordinary skill in the art.

BRIEF SUMMARY OF THE INVENTION

The present invention provides a method of flattening a substrate, where the method has advantages of etching a substrate with an etching solution without influencing the following processes.

An exemplary embodiment of the present invention provides a method of flattening a substrate, including, forming a metal layer on an upper surface of a substrate, forming a photoresist layer overlapping the substrate and the metal layer, radiating light to the photoresist layer, through a lower surface of the substrate opposite to the upper surface, exposing the metal layer by developing the photoresist layer, exposing the upper surface of the substrate by etching the metal layer, etching the exposed upper surface of the substrate, and removing the photoresist layer.

The radiating light to the photoresist layer may use the metal layer as a mask.

The metal layer may include a double layer comprising an upper layer and a lower layer, the lower layer may include titanium (Ti) and the upper layer may include copper (Cu).

The forming the metal layer on the upper surface of the substrate may include stacking a lower metal layer on the substrate, stacking an upper metal layer on the lower metal layer, forming a photoresist pattern on the upper metal layer, etching the upper metal layer and the lower metal layer with a first etchant using the photoresist pattern as a mask, and removing the photoresist pattern. In the etching the upper metal layer and the lower metal layer with a first etchant, a step portion of the substrate may be formed between a portion of the substrate which overlaps the lower metal layer and a portion of the substrate which is not covered by the photoresist pattern.

The first etchant may contain fluoric acid.

The photoresist layer may be a negative type.

The forming the metal layer on the upper surface of the substrate includes forming a step portion of the substrate, and the etching the exposed upper surface of the substrate removes the step portion of the substrate.

The etching the exposed upper surface of the substrate may use an etchant containing fluoric acid.

The substrate may be flattened or planarized, after the etching the exposed upper surface of the substrate.

Another exemplary embodiment of the present invention provides a method of manufacturing a thin film transistor array panel, including forming a first gate line on an upper surface of a substrate, forming a photoresist layer overlapping the substrate and the first gate line, radiating light to the photoresist layer, through a lower surface of the substrate opposite to the upper surface, exposing the first gate line by developing the photoresist layer, exposing the upper surface of the substrate by etching the first gate line, etching the exposed upper surface of the substrate, removing the photoresist layer, forming a second gate line on the substrate, forming a gate insulating layer on the second gate line, forming a semiconductor layer on the gate insulating layer, forming a data line including a source electrode and a drain electrode on the semiconductor layer, forming a passivation layer on the data line and the drain electrode, the passivation layer including a contact hole, and forming a pixel electrode connected with the drain electrode through the contact hole, on the passivation layer.

The radiating light to the photoresist layer may use the first gate line as a mask.

The first gate line and the second gate line may each include a double layer comprising an upper layer and a lower layer, the lower layer may including titanium (Ti), and the upper layer may including copper (Cu).

The forming the first gate line on the upper surface of the substrate may include stacking a lower metal layer on the substrate, stacking an upper metal layer on the lower metal layer, forming a photoresist pattern on the upper metal layer, etching the upper metal layer and the lower metal layer with

a first etchant, using the photoresist pattern as a mask, and removing the photoresist pattern. In the etching the upper metal layer and the lower metal layer with a first etchant, a step portion of the substrate may be formed between a portion of the substrate which overlaps the lower metal layer and the portion of the substrate which is not overlapped by the photoresist pattern.

The first etchant may contain fluoric acid.

The photoresist layer may be a negative type.

The forming the first gate line on the upper surface of the substrate includes forming a step portion of the substrate, and the etching the exposed upper surface of the substrate removes the step portion.

The etching the exposed upper surface of the substrate may use an etchant containing fluoric acid.

The substrate may be flattened or planarized, after the etching the exposed upper surface of the substrate, and before the forming the second gate line on the upper surface of the substrate.

According to exemplary embodiments of the present invention, it is possible to solve the problem of stains in the following processes by flattening the substrate by using rear exposure.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other aspects and features of this disclosure will become more apparent by describing in further detail exemplary embodiments thereof with reference to the accompanying drawings, in which:

FIG. 1 to FIG. 7 are cross-sectional views illustrating an exemplary embodiment of a flattening method of a substrate according to the present invention.

FIG. 8 is a flowchart illustrating an exemplary embodiment of a method of manufacturing a thin film transistor array panel according to the present invention.

FIG. 9 is a top plan view showing an exemplary embodiment of a portion of the thin film transistor array panel manufactured by the method of FIG. 8.

FIG. 10 is a cross-sectional view taken along line X-X' of FIG. 9.

DETAILED DESCRIPTION OF THE INVENTION

The present invention will be described more fully herein after with reference to the accompanying drawings, in which exemplary embodiments of the invention are shown. As those skilled in the art would realize, the described embodiments may be modified in various different ways, all without departing from the spirit or scope of the present invention. The exemplary embodiments proposed herein are provided to make the description clearly and fully understood, and to sufficiently provide the scope of the present invention to a person of an ordinary skill in the art.

The thickness of layers and regions may be exaggerated for clarity in the drawings. Further, when a layer is referred to as being "on" another layer or a substrate, it can be directly on the other element of the substrate or intervening layers may also be present. Like reference numerals designate like elements throughout the specification.

It will be understood that, although the terms first, second, third, etc., may be used herein to describe various elements, components, regions, layers and/or sections, these elements, components, regions, layers and/or sections should not be limited by these terms. These terms are only used to distinguish one element, component, region, layer or section from another region, layer or section. Thus, a first element, com-

ponent, region, layer or section discussed below could be termed a second element, component, region, layer or section without departing from the teachings of the invention.

Spatially relative terms, such as "lower," "under," "above," "upper" and the like, may be used herein for ease of description to describe the relationship of one element or feature to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation, in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as "lower" or "under" relative to other elements or features would then be oriented "above" relative to the other elements or features. Thus, the exemplary term "under" can encompass both an orientation of above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly.

The terminology used herein is for the purpose of describing particular embodiments only and is not intended to be limiting of the invention. As used herein, the singular forms "a," "an" and "the" are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will be further understood that the terms "comprises" and/or "comprising," when used in this specification, specify the presence of stated features, integers, steps, operations, elements, and/or components, but do not preclude the presence or addition of one or more other features, integers, steps, operations, elements, components, and/or groups thereof.

Embodiments of the invention are described herein with reference to cross-section illustrations that are schematic illustrations of idealized embodiments (and intermediate structures) of the invention. As such, variations from the shapes of the illustrations as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, embodiments of the invention should not be construed as limited to the particular shapes of regions illustrated herein but are to include deviations in shapes that result, for example, from manufacturing.

Unless otherwise defined, all terms (including technical and scientific terms) used herein have the same meaning as commonly understood by one of ordinary skill in the art to which this invention belongs. It will be further understood that terms, such as those defined in commonly used dictionaries, should be interpreted as having a meaning that is consistent with their meaning in the context of the relevant art and will not be interpreted in an idealized or overly formal sense unless expressly so defined herein.

All methods described herein can be performed in a suitable order unless otherwise indicated herein or otherwise clearly contradicted by context. The use of any and all examples, or exemplary language (e.g., "such as"), is intended merely to better illustrate the invention and does not pose a limitation on the scope of the invention unless otherwise claimed. No language in the specification should be construed as indicating any non-claimed element as essential to the practice of the invention as used herein.

Hereinafter, the invention will be described in detail with reference to the accompanying drawings.

FIG. 1 to FIG. 7 are cross-sectional views illustrating an exemplary embodiment of a flattening method of a substrate according to the present invention.

Referring to FIG. 1, a lower metal layer 110 and an upper metal layer 120 are sequentially formed on an upper surface of a substrate 100. The lower metal layer 110 may include titanium or a titanium alloy, and the upper metal layer 120 may include copper or a copper alloy. The lower metal layer

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110 may have a thickness of about 10 angstroms (Å) to about 150 Å, and the upper metal layer **120** may have a thickness of 2000 Å to 5000 Å. The thicknesses are taken perpendicular to the substrate **100**.

Referring to FIG. 2, a lower layer **110_p** and an upper layer **120_p** sequentially stacked on the substrate **100** are formed by collectively etching the upper metal layer **120** and the lower metal layer **110**, such as by using photolithography. In detail, a photoresist pattern (not shown) is formed overlapping the upper metal layer **120**, and the upper metal layer **120** and the lower metal layer **110** are etched at substantially a same time by using the photoresist pattern as a mask. The photoresist pattern may be formed overlapping only the upper metal layer **120**, and may extend at a maximum to outer edges of (e.g., aligned with outer edges) the upper metal layer **120**. An etchant containing fluoric acid may be used to collectively etch the upper metal layer **120** and the lower metal layer **110** in forming the lower layer **110_p** and the upper layer **120_p** of a wire portion.

A portion of the substrate **100** may also be etched in the process of etching the upper metal layer **120** and the lower etching layer **110**. Therefore, a step may be formed between the portion of the substrate **100** which overlaps the lower metal layer **110** (e.g., aligns with outer edges of the lower metal layer **110**) and the portion of the substrate **100** which is not overlapped by the photoresist pattern. A thickness *d* of the etched portion of the substrate **100** may be about 300 Å to about 400 Å.

The upper layer **120_p** and the lower layer **110_p** may each have a tapered lateral side, and may be inclined at an angle between 0 degrees and about 50 degrees, with respect to the substrate **100**.

Referring to FIG. 3, a photoresist layer PR is formed to cover (e.g., overlap) the etched portion of the substrate **100**, the lower layer **110_p**, and the upper layer **120_p**. Then, the photoresist layer PR is exposed by radiating light L through a lower surface of the substrate **100**. That is, the photoresist layer PR is exposed by performing rear exposure, using a metal layer including the lower layer **110_p** and the upper layer **120_p**, as a mask. The photo resist layer PR is a negative type photoresist.

Referring to FIG. 4, a portion of the photoresist layer PR remains where the light is radiated and the upper layer **120_p** and the lower layer **110_p** are not disposed. A portion of the photoresist layer PR which overlaps the lower layer **110_p** is removed.

As the portion of the photoresist layer PR overlapping the lower layer **110_p** is removed, the upper layer **120_p** and the lower layer **110_p** are exposed. The photoresist layer PR is a negative type, and the remaining portion of the photoresist layer PR has an inverse tapered shape as a result of the rear exposure.

Referring to FIG. 5, the exposed upper layer **120_p** and the lower layer **110_p** are sequentially etched and removed, such as by an etchant. The etchant used in this process may be the same as the etchant that is used to collectively etch the upper metal layer **120** and the lower metal layer **110** in FIG. 2.

Referring to FIG. 6, the upper surface of the substrate **100** which is exposed by over-etching may be subsequently etched, after the upper layer **120_p** and the lower layer **110_p** are etched and removed. In this process, the step portion of the substrate **100** between the lower metal layer **110** and a remaining portion of the substrate **100** which has been formed in the process described with reference to FIG. 2, can be removed. The thickness *d* indicated by the dotted line in FIG. 6, illustrates where the removed step portion of the substrate **100** was located prior to etching.

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Referring to FIG. 7, a flattened substrate **100** is formed by developing the photoresist layer PR and removing the remaining photoresist layer PR. The flattened substrate **100** includes a continuous planar upper surface which is planarized after the upper layer **120_p** and the lower layer **110_p** are etched and removed.

The flattening method of a substrate that has been described above with reference to FIG. 1 to FIG. 7 may be applied to a reprocess of forming the wiring pattern again, after removing the wiring pattern such as due to a problem in the initially formed the wire pattern.

FIG. 8 is a flowchart illustrating an exemplary embodiment of a method of manufacturing a thin film transistor (“TFT”) array panel according to the present invention. FIG. 9 is a top plan view showing the TFT array panel manufactured by the method of FIG. 8. FIG. 10 is a cross-sectional view taken along line X-X' of FIG. 9.

Referring to FIG. 8 to FIG. 10, a first gate line is initially formed on an insulation substrate **110** including transparent glass or plastic (**S10**). The first gate line includes a lower layer and an upper layer. A plurality of the first gate line may be formed on the insulation substrate **110**.

In detail, a lower metal layer and an upper metal layer are sequentially stacked on the insulation substrate **110**, and then the upper metal layer and the lower metal layer are collectively etched such as by photolithography, thereby forming the first gate lines each including the lower layer and the upper layer sequentially stacked on the insulation substrate **110**.

The first gate lines may be formed incorrectly or be defective in an initial process of forming the first gate lines. When the first gate lines are formed incorrectly or are defective, a reprocess may be performed, as described above in the exemplary embodiment shown in FIG. 3 to FIG. 7.

In other words, for the reprocess, a photoresist layer is formed directly on upper and side surfaces of the insulation substrate **110** and the first gate lines, respectively. (**S20**). Further, light is radiated through a bottom of the insulation substrate **110** (**S30**), and portions of the first gate lines are exposed by developing the photoresist layer (**S40**).

Thereafter, the exposed first gate lines are removed by etching, and a portion of the upper surface of the insulation substrate **110** is exposed (**S50**). Further, the photoresist layer is removed (**S70**), after the top of the exposed insulation substrate **110** is etched (**S60**). A substrate **110** including an entirely planar upper surface (e.g., a flattened substrate) is formed by the removing the first gate lines (**S50**), the etching of a stepped portion of the substrate using the remaining portion of the photoresist layer (**S60**) and removing the remaining portion of the photoresist layer (**S70**).

A plurality of second gate lines **121** is formed on the insulation substrate **110** that has been previously flattened in the processes described above (**S80**).

The second gate lines **121** transmit gate signals and are extended in a first direction, such as a horizontal direction in the plan view of FIG. 9. The gate lines **121** each include a plurality of gate electrodes **124** protruding from the gate lines **121**. A gate line **121** and the gate electrodes **124** protruding therefrom, collectively form a single, unitary indivisible member. The gate lines **121** and the gate electrodes **124** may be considered as the gate wire of the TFT array panel.

The gate line **121** and the gate electrode **124** each have a dual-layer structure, such as including a lower layer **124_p** and an upper layer **124_r**. The lower layer **124_p** includes titanium (Ti) or a titanium alloy, and the upper layer **124_r** includes copper (Cu) or a copper alloy.

A gate insulating layer **140** including an insulating material, such as silicon nitride, is formed on the gate line **121** (S90).

A semiconductor layer **151** including hydrogenated amorphous silicon or polycrystalline silicon, is formed on the gate insulating layer **140** (S100).

The semiconductor layer **151** longitudinally extend in the first direction and have a plurality of projections **154** extending toward the gate electrode **124**.

A plurality of ohmic contact stripes **161** and ohmic contact islands **165** are formed on the projections **154** of the semiconductor layer **151**. The ohmic contact stripes **161** have a plurality of projections **163**, and the projections **163** and the ohmic contact islands **165** are respectively disposed in pairs on the projections **154** of the semiconductor layer **151**.

A plurality of data lines **171** and a plurality of drain electrodes **175** are formed on the ohmic contacts **161** and **165**, and on the gate insulating layer **140** (S110). The data lines **171** and the drain electrodes **175** may be considered as the data wire of the TFT array panel.

The data line **171** transmits data signals and extends longitudinally in a second direction different from the first direction, and intersects the gate line **121**. Each of the data line **171** includes a plurality of source electrodes **173** extending in a U-shape toward the gate electrode **124**, in the plan view.

The drain electrode **175** is separated from the data line **171**, and extends in the second direction at a middle portion of the U-shape of the source electrode **173** in the plan view.

The data line **171** including the source electrode **173**, and the drain electrode **175**, also have a dual-layer structure including the upper layers **171r**, **173r**, and **175r** and the lower layers **171p**, **173p**, and **175p**. The upper layers **171r**, **173r**, and **175r** include copper (Cu) or a copper alloy, and the lower layers **171p**, **173p**, and **175p** include one of titanium (Ti), tantalum (Ta), molybdenum (Mo), and an alloy thereof.

The lower layers **171p**, **173p**, and **175p**, and the upper layers **171r**, **173r**, and **175r**, of the data line **171** and the drain electrode **175**, respectively, each have a tapered lateral side in a cross-sectional view.

The ohmic contacts **161**, **163**, and **165** are only in between the semiconductors **151** and **154** thereunder, and the lower layers **171p**, **173p**, and **175p** of the data line **171** and the drain electrode **175** thereabove. The ohmic contacts **161**, **163**, and **165** reduce contact resistance between the semiconductors **151** and **154**, and the lower layers **171p**, **173p**, and **175p**, respectively. Further, the ohmic contacts **161**, **163**, and **165** may have substantially the same plane pattern as the lower layers **171p**, **173p**, and **175p** of the data lines **171** and the drain electrodes **175**, respectively.

In addition, a portion of the semiconductor layer **151** between the source electrode **173** and the drain electrode **175** is exposed, and not overlapped by the data line **171** and the drain electrode **175**. The exposed portion is formed at the projection **154** of the semiconductor layer **151**. The semiconductor layer **151** may have substantially the same plane pattern as the ohmic contacts **161** and **165**, except for the exposed portion of the projection **154**.

One gate electrode **124**, one source electrode **173**, and one drain electrode **175** constitute one TFT, together with the projection **154** of the semiconductor layer **151**. The channel of the TFT is defined at the exposed portion of the projection **154** between the source electrode **173** and the drain electrode **175**.

A passivation layer **180** is formed on the data line **171**, the drain electrode **175**, and the projection **154** of the exposed semiconductor layer (S120).

The passivation layer **180** includes an inorganic insulator, such as silicon nitride or silicon oxide, an organic insulator, or a low dielectric insulator.

The passivation layer **180** directly contacts portions of an upper surface of the lower layers **171p**, **173p**, and **175p** which are partially exposed from the outer edges of the upper layers **171r**, **173r**, and **175r**, and portions of surfaces of the semiconductor layer **151** partially exposed from the horizontal outer edges of the lower layers **171p**, **173p**, and **175p**.

A plurality of contact holes **185** exposing ends of the drain electrodes **175** is formed extending completely through a thickness of the passivation layer **180**.

A plurality of pixel electrodes **191** is formed on the passivation layer **180** (S130).

The pixel electrode **191** may include a transparent conductor, such as indium tin oxide ("ITO") or indium zinc oxide ("IZO").

The pixel electrode **191** is physically and electrically connected with the drain electrode **175** through the contact hole **185**, and receives data voltage from the drain electrode **175**. The pixel electrode **191** that has received the data voltage generates an electric field, together with a common electrode (not shown) which receives common voltage, thereby determining the direction of the liquid crystal molecules in the liquid crystal layer (not shown) between the two electrodes. The common electrode but may be formed on a display panel opposing the TFT array panel, or alternative on the TFT array panel. The pixel electrode **191** and the common electrode collectively constitute a capacitor (hereafter, referred to as a "liquid crystal capacitor") to keep the voltage even after the TFT is turned off.

The pixel electrode **191** may form a storage capacitor by overlapping a storage electrode line (not shown), such that the performance of the liquid crystal capacitor which keeps the voltage can be improved.

While this invention has been described in connection with what is presently considered to be practical exemplary embodiments, it is to be understood that the invention is not limited to the disclosed embodiments, but, on the contrary, is intended to cover various modifications and equivalent arrangements included within the spirit and scope of the appended claims.

What is claimed is:

1. A method of flattening a substrate, the method comprising:
 - forming a metal layer on an upper surface of a substrate;
 - forming a photoresist layer overlapping the substrate and the metal layer;
 - radiating light to the photoresist layer, through a lower surface of the substrate opposite to the upper surface;
 - exposing the metal layer by developing the photoresist layer;
 - exposing the upper surface of the substrate by etching the metal layer;
 - etching the exposed upper surface of the substrate; and
 - removing the photoresist layer.
2. The method of claim 1, wherein:
 - the radiating light to the photoresist layer uses the metal layer as a mask.
3. The method of claim 2, wherein
 - the metal layer includes a double layer comprising an upper layer and a lower layer, the lower layer including titanium (Ti) and the upper layer including copper (Cu).
4. The method of claim 3, wherein:
 - the forming the metal layer on the upper surface of the substrate includes:
 - stacking a lower metal layer on the substrate;

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stacking an upper metal layer on the lower metal layer;
forming a photoresist pattern on the upper metal layer;
etching the upper metal layer and the lower metal layer
with a first etchant, using the photoresist pattern as a
mask; and

removing the photoresist pattern,

wherein in the etching the upper metal layer and the
lower metal layer with a first etchant, a step portion of
the substrate is formed between a portion of the sub-
strate which overlaps the lower metal layer and a
portion of the substrate which is not overlapped by the
photoresist pattern.

5. The method of claim 4, wherein:

the first etchant contains fluoric acid.

6. The method of claim 5, wherein:

the photoresist layer is a negative type.

7. The method of claim 1, wherein:

the forming the metal layer on the upper surface of the
substrate includes forming a step portion of the sub-
strate, and

the etching the exposed upper surface of the substrate
removes the step portion.

8. The method of claim 7, wherein:

the etching the exposed upper surface of the substrate uses
an etchant containing fluoric acid.

9. The method of claim 8, wherein:

the upper surface of the substrate is planarized, after the
etching the exposed upper surface of the substrate.

10. A method of manufacturing a thin film transistor array
panel, the method comprising:

forming a first gate line on an upper surface of a substrate;
forming a photoresist layer overlapping the substrate and
the first gate line;

radiating light to the photoresist layer, through a lower
surface of the substrate opposite to the upper surface;
exposing the first gate line by developing the photoresist
layer;

exposing the upper surface of the substrate by etching the
first gate line;

etching the exposed upper surface of the substrate;

removing the photoresist layer;

forming a second gate line on the upper surface of the
substrate;

forming a gate insulating layer on the second gate line;

forming a semiconductor layer on the gate insulating layer;

forming a data line including a source line and a drain
electrode, on the semiconductor layer;

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forming a passivation layer on the data line and the drain
electrode, the passivation layer including a contact hole;
and

forming a pixel electrode connected with the drain elec-
trode through the contact hole, on the passivation layer.

11. The method of claim 10, wherein:

the radiating light to the photoresist layer uses the first gate
line as a mask.

12. The method of claim 11, wherein:

the first gate line and the second gate line each include a
double layer comprising an upper layer and a lower
layer, the lower layer including titanium (Ti), and the
upper layer including copper (Cu).

13. The method of claim 12, wherein:

the forming the first gate line on the upper surface of the
substrate includes:

stacking a lower metal layer on the substrate;

stacking an upper metal layer on the lower metal layer;

forming a photoresist pattern on the upper metal layer;

etching the upper metal layer and the lower metal layer
with a first etchant, using the photoresist pattern as a
mask; and

removing the photoresist pattern,

wherein in the etching the upper metal layer and the
lower metal layer with a first etchant, a step portion of
the substrate is formed between a portion of the sub-
strate which overlaps the lower metal layer and a
portion of the substrate which is not overlapped by the
photoresist pattern.

14. The method of claim 13, wherein:

the first etchant contains fluoric acid.

15. The method of claim 14, wherein:

the photoresist layer is a negative type.

16. The method of claim 10, wherein:

the forming the first gate line on the upper surface of the
substrate includes forming a step portion of the sub-
strate, and

the etching the exposed upper surface of the substrate
removes the step portion.

17. The method of claim 16, wherein:

the etching the exposed upper surface of the substrate uses
an etchant containing fluoric acid.

18. The method of claim 17, wherein:

the upper surface of substrate is planarized, after the etch-
ing the exposed upper surface of the substrate, and
before the forming the second gate line on the upper
surface of the substrate.

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